

### 描述 / Descriptions

TO-3P 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-3P Plastic Package.

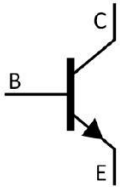
### 特征 / Features

耐压高、速度快和安全工作区宽。  
High breakdown voltage, high speed, wide SOA.

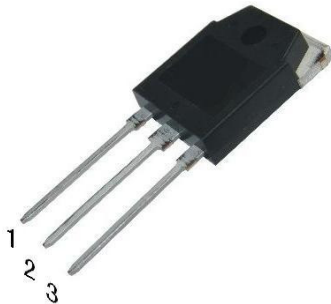
### 用途 / Applications

用于电视、CRT 显示器的水平偏转输出。  
Horizontal deflection output for TV and CRT monitor.

### 内部等效电路 / Equivalent Circuit



### 引脚排列 / Pinning



PIN1 : Base      PIN 2 : Collector      PIN 3 : Emitter

### 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。See Marking Instructions.

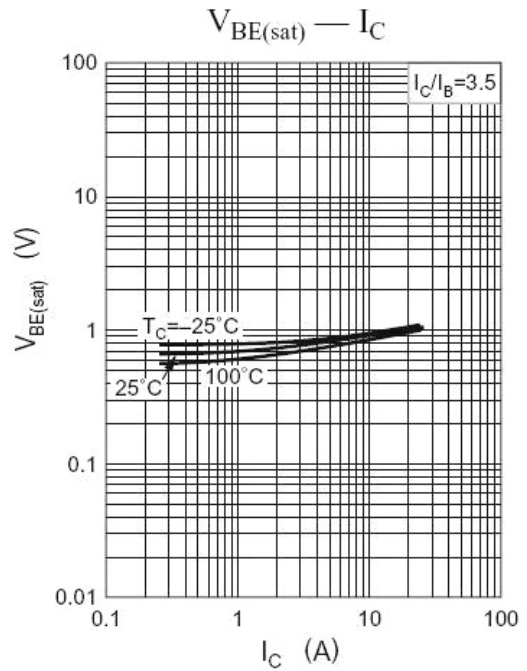
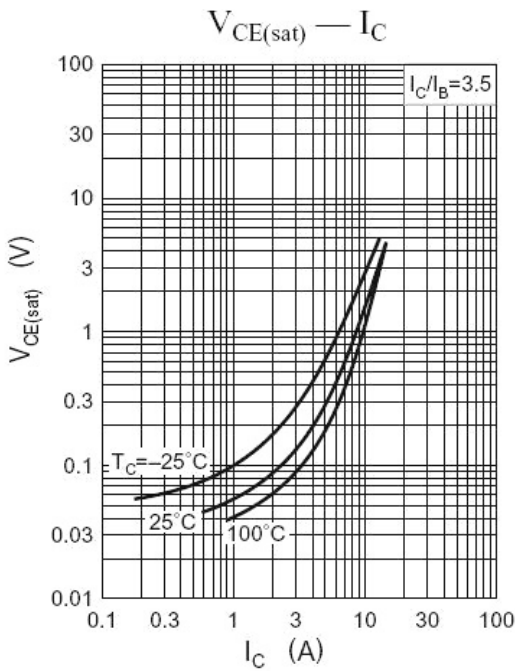
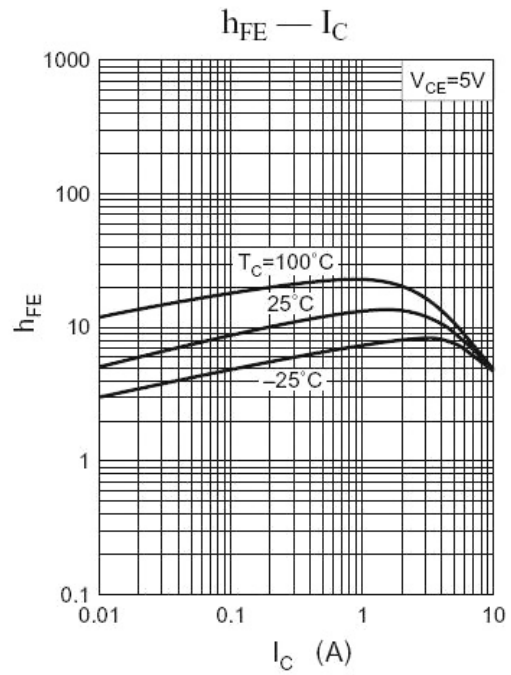
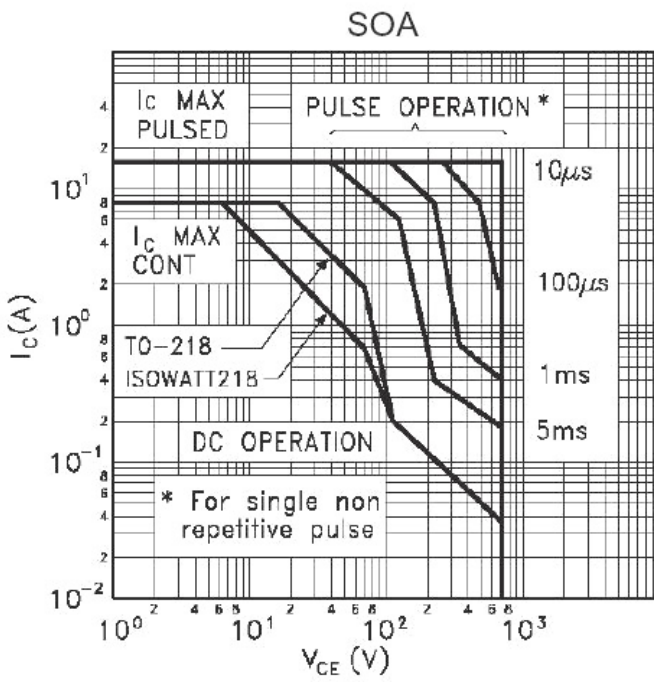
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

| 参数<br>Parameter                | 符号<br>Symbol            | 数值<br>Rating | 单位<br>Unit |
|--------------------------------|-------------------------|--------------|------------|
| Collector to Base Voltage      | $V_{CBO}$               | 1500         | V          |
| Collector to Emitter Voltage   | $V_{CES}$               | 1500         | V          |
| Collector to Emitter Voltage   | $V_{CEO}$               | 800          | V          |
| Emitter to Base Voltage        | $V_{EBO}$               | 6            | V          |
| Collector Current - Continuous | $I_C$                   | 20           | A          |
| Peak Collector Current         | $I_{CP}$                | 30           | A          |
| Base Current                   | $P_C$                   | 3            | W          |
| Collector Power Dissipation    | $P_{C(TC=25^{\circ}C)}$ | 200          | W          |
| Junction Temperature           | $T_j$                   | 150          | °C         |
| Storage Temperature Range      | $T_{stg}$               | -55~150      | °C         |

**电性能参数 / Electrical Characteristics(Ta=25°C)**

| 参数<br>Parameter                         | 符号<br>Symbol  | 测试条件<br>Test Conditions               | 最小值<br>Min | 典型值<br>Typ | 最大值<br>Max | 单位<br>Unit |
|---|---------------|---------------------------------------|------------|------------|------------|------------|
| Collector to Base Breakdown Voltage     | $V_{CBO}$     | $I_C=1mA$ $I_E=0$                     | 1500       |            |            | V          |
| Collector to Base Breakdown Voltage     | $V_{CEO}$     | $I_C=10mA$ $I_B=0$                    | 800        |            |            | V          |
| Collector to Emitter Breakdown Voltage  | $V_{EBO}$     | $I_E=1mA$ $I_C=0$                     | 6          |            |            | V          |
| Collector Cut-Off Current               | $I_{CBO}$     | $V_{CB}=1500V$ $I_E=0$                |            |            | 1          | mA         |
| Collector Cut-Off Current               | $I_{CEO}$     | $V_{CB}=800V$ $I_E=0$                 |            |            | 1          | mA         |
| Emitter Cut-Off Current                 | $I_{EBO}$     | $V_{EB}=5V$ $I_C=0$                   |            |            | 50         | μA         |
| DC Current Gain                         | $h_{FE(1)}$   | $V_{CE}=5V$ $I_C=1A$                  | 10         |            | 30         |            |
|   | $h_{FE(2)}$   | $V_{CE}=5V$ $I_C=1mA$                 | 8          |            | 30         |            |
|   | $h_{FE(3)}$   | $V_{CE}=5V$ $I_C=10A$                 | 5          |            | 12         |            |
| Collector to Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=10A$ $I_B=2.8A$                  |            |            | 3          | V          |
| Base to Emitter Saturation Voltage      | $V_{BE(sat)}$ | $I_C=10A$ $I_B=2.8A$                  |            |            | 1.5        | V          |
| Transition Frequency                    | $f_T$         | $V_{CE}=10V$ $I_C=0.1A$<br>$f=0.5MHz$ |            | 3          |            | MHz        |
| Storage Time                            | $t_s$         | $V_{CE}=5V$ $I_C=0.5A$<br>UI9600      |            | 6.5        |            | μs         |
| Fall Time                               | $t_f$         |                                       |            | 1          |            | μs         |

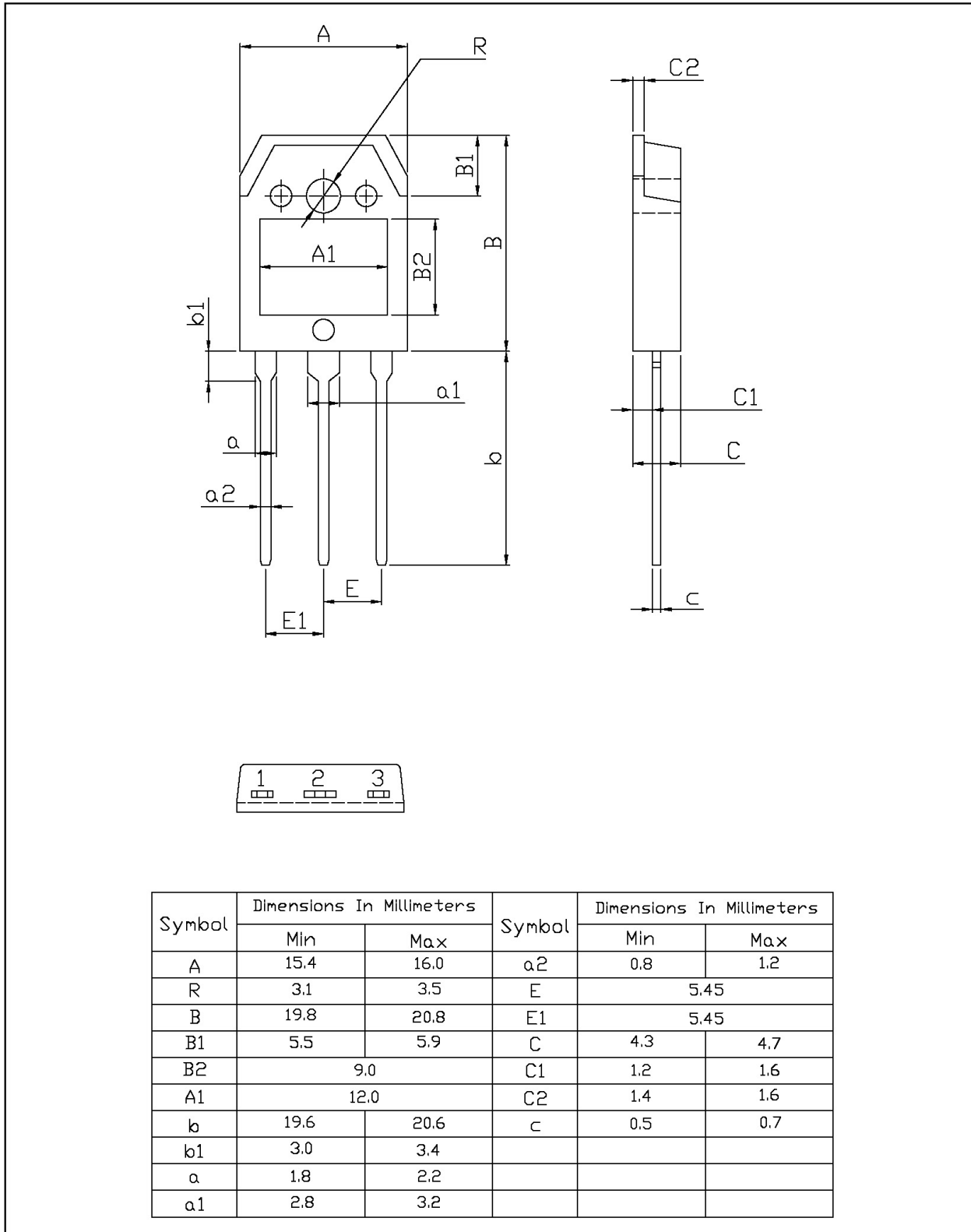
电参数曲线图 / Electrical Characteristic Curve



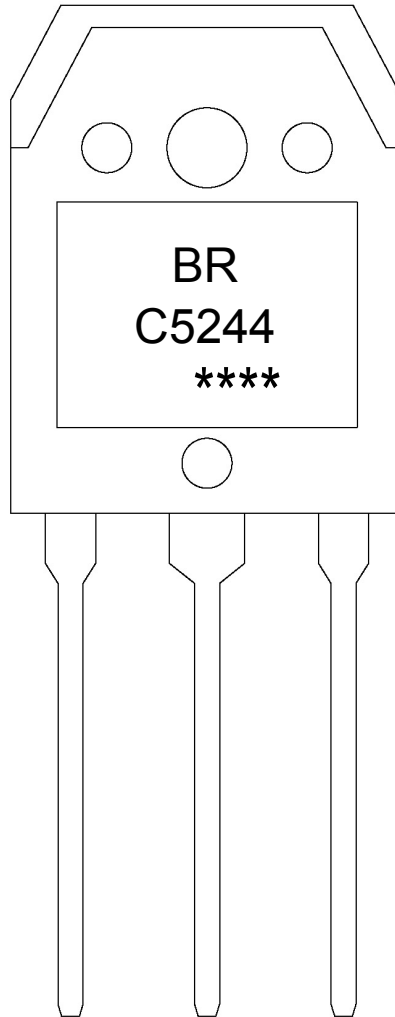
外形尺寸图 / Package Dimensions

TO-3P

单位: mm



印章说明 / Marking Instructions



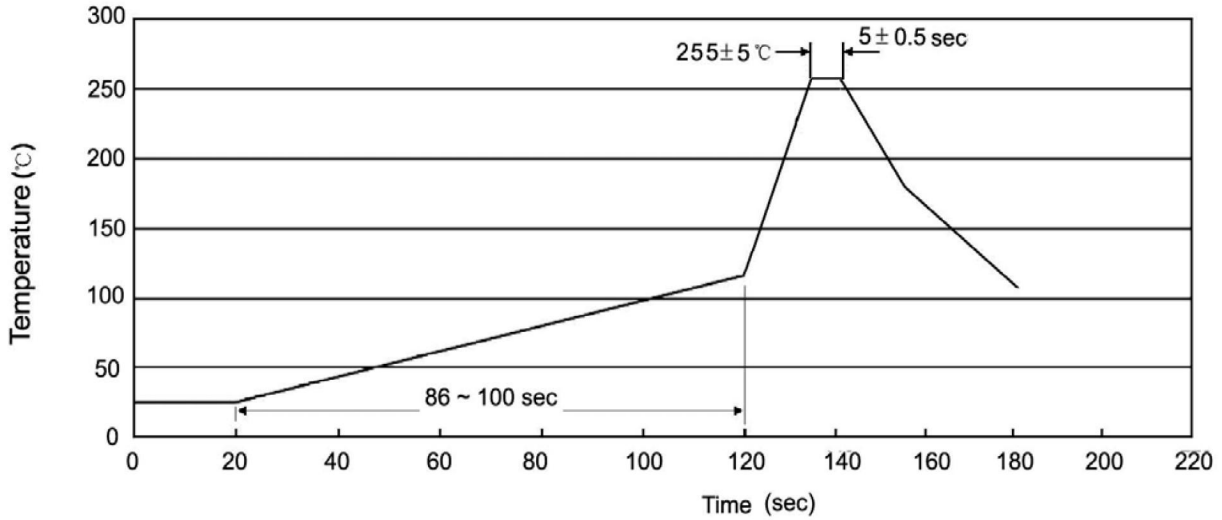
说明：

BR: 为公司代码  
C5244 : 为型号代码  
\*\*\*\* : 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.  
C5244: Product Type.  
\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C      时间：10±1 sec.      Temp.:270±5°C      Time:10±1 sec

**包装规格 / Packaging SPEC.**

套管包装 / TUBE

| Package Type<br>封装形式 | Units 包装数量         |                         |                        |                              |                        | Dimension 包装尺寸 (unit: mm <sup>3</sup> ) |             |             |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|---|-------------|-------------|
|                      | Units/Tube<br>只/套管 | Tubes/Inner Box<br>套管/盒 | Units/Inner Box<br>只/盒 | Inner Boxes/Outer Box<br>盒/箱 | Units/Outer Box<br>只/箱 | Tube 套管                                 | Inner Box 盒 | Outer Box 箱 |
| TO-3P                | 30                 | 15                      | 450                    | 5                            | 2250                   | 497.5×46×8                              | 555×164×50  | 575×290×180 |

**使用说明 / Notices**